

preliminary data

$$I_{FAVM} = 2 \times 128 \text{ A}$$

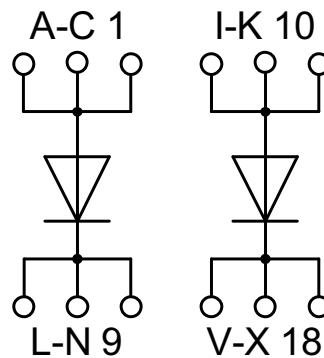
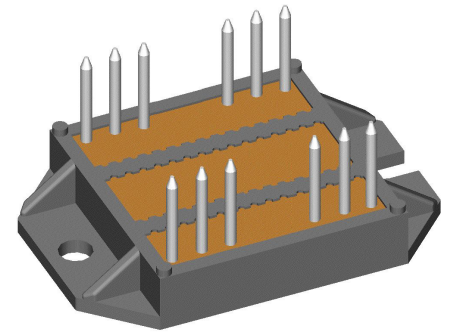
$$V_{RRM} = 1200 \text{ V}$$

$$t_{rr} = 40 \text{ ns}$$

Fast Recovery Epitaxial Diode (FRED)

Part number

DSEI2x161-12P



Features / Advantages:

- 2 independent FRED in 1 package
- Planar passivated chips
- Very short recovery time
- Leads suitable for PC board soldering
- Very short recovery time
- Soft recovery behaviour
- Easy to mount with two screws
- Space and weight savings
- Improved temperature and power cycling capability
- Low noise switching
- Small and light weight

Applications:

- Antiparallel diode for high frequency switching devices
- Anti saturation diode
- Snubber diode
- Free wheeling diode in converters and motor control circuits
- Rectifiers in switch mode power supplies (SMPS)
- Inductive heating and melting
- Uninterruptible power supplies (UPS)
- Ultrasonic cleaners and welders

Package: ECO-PAC2

- Isolation voltage: 3000 V~
- Industry standard outline
- RoHS compliant
- Soldering pins for PCB mounting
- Height: 9 mm
- Base plate: DCB ceramic
- Reduced weight
- Advanced power cycling

Disclaimer Notice

Information furnished is believed to be accurate and reliable. However, users should independently evaluate the suitability of and test each product selected for their own applications. Littelfuse products are not designed for, and may not be used in, all applications. Read complete Disclaimer Notice at www.littelfuse.com/disclaimer-electronics.

preliminary data

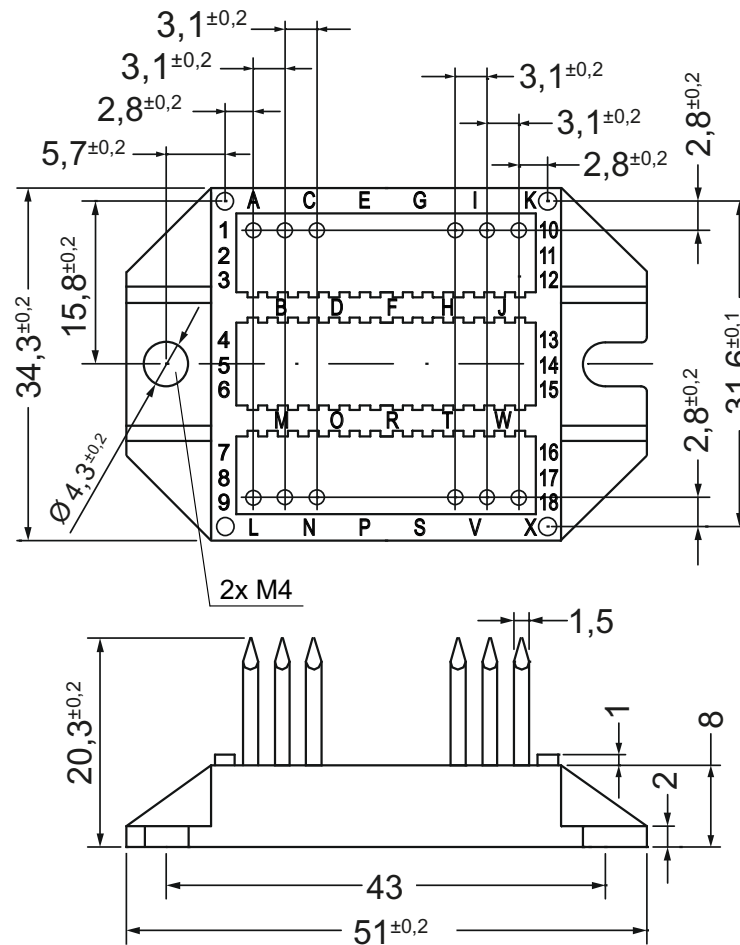
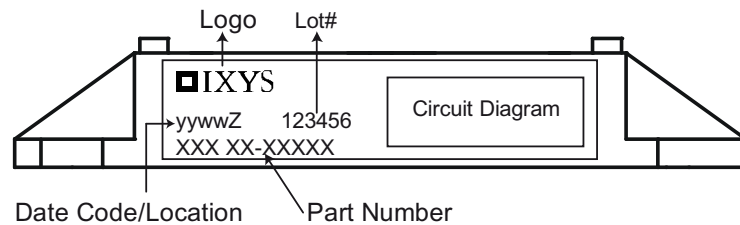
Diode				Ratings		
Symbol	Definitions	Conditions	min.	typ.	max.	
I_{FRMS}	RMS forward current				270	A
I_{FAVM} ①	max. average forward current	rectangular, d = 0.5			128	A
I_{FSM}	max. surge forward current	t = 10 ms (50 Hz), sine	$T_{VJ} = 45^{\circ}\text{C}$		1200	A
		t = 8.3 ms (60 Hz), sine			1300	A
		t = 10 ms (50 Hz), sine	$T_{VJ} = 150^{\circ}\text{C}$		1080	A
		t = 8.3 ms (60 Hz), sine			1170	A
I^2t	I^2t value for fusing	t = 10 ms (50 Hz), sine	$T_{VJ} = 45^{\circ}\text{C}$		7200	A ² s
		t = 8.3 ms (60 Hz), sine			7100	A ² s
		t = 10 ms (50 Hz), sine	$T_{VJ} = 150^{\circ}\text{C}$		5800	A ² s
		t = 8.3 ms (60 Hz), sine			5700	A ² s
I_R	reverse current	$V_R = V_{RRM}$	$T_{VJ} = 25^{\circ}\text{C}$		12	mA
		$V_R = 0.8 \cdot V_{RRM}$	$T_{VJ} = 25^{\circ}\text{C}$		3	mA
		$V_R = 0.8 \cdot V_{RRM}$	$T_{VJ} = 125^{\circ}\text{C}$		60	mA
V_F	forward voltage	$I_F = 200\text{ A}$	$T_{VJ} = 25^{\circ}\text{C}$		1.9	V
V_{TO}	threshold voltage	for power-loss calculations only	$T_{VJ} = T_{VJM}$		1.16	V
r_T	slope resistance				3	mΩ
R_{thJC}	thermal resistance junction to case			0.20	0.29	K/W
R_{thCH}	thermal resistance junction to heatsink					K/W
I_{RM}	max. reverse recovery current	$I_F = 100\text{ A}$; $-di_F/dt = 200\text{ A}/\mu\text{s}$ $V_R = 100\text{ V}$; $L \leq 0.05\ \mu\text{H}$	$T_{VJ} = 100^{\circ}\text{C}$		48	A
t_{rr}	reverse recovery time	$I_F = 1\text{ A}$; $-di/dt = 400\text{ A}/\mu\text{s}$; $V_R = 30\text{ V}$	$T_{VJ} = 25^{\circ}\text{C}$		40	ns

 ① I_{FAVM} rating includes reverse blocking losses at T_{VJM} , $V_R = 0.8 V_{RRM}$, duty cycle d = 0.5



preliminary data

Package ECO-PAC2			Ratings			
Symbol	Definitions	Conditions	min.	typ.	max.	
I_{RMS}	RMS current	per terminal			100	A
T_{VJ}	virtual junction temperature		-40		150	°C
T_{op}	operation temperature		-40		125	°C
T_{stg}	storage temperature		-40		125	°C
Weight				24		g
M_D	mounting torque		1.4		2.0	Nm
$d_{Spp/App}$	creepage distance on surface striking distance through air	terminal to terminal	6.0			mm
$d_{Spb/Appb}$			terminal to backside	10.0		
V_{ISOL}	isolation voltage	t = 1 second t = 1 minute	3000 2500			V V
			50/60 Hz, RMS; $I_{ISOL} \leq 1$ mA			



IXYS reserves the right to change limits, conditions and dimensions.

Data according to IEC 60747 and per semiconductor unless otherwise specified.

20220615b